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Figs. 11a through 11c show a top view of the PAR implementation, applied to second two-dimensional features.

Fig. 12 shows a top view of two packing features per side, as applied in the top view shown in Figs. 2a through 2c.

Fig. 13 shows a top view of a two-dimensional double Full Size Assist Feature (FSAF).

Figs. 14a through 14c show a top view of an unpacking mask, required for the desired features as shown in top view in Figs. 1a through 1c.

Figs. 15a through 20 address a new method to enhance Critical Diameter (CD) uniformity in the manufacturing of Integrated Circuit (IC) devices, as follows:

15 15
Figs. ~~13~~a through ~~13~~d show prior art methods with and without Critical Diameter uniformity.

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Figs. 16a through 16f show the creation of a main pattern and an isolated pattern, using correction of optimal proximity effect and micro-loading that is provided by the invention.